

Ab initio and full-zone $k \cdot p$ computations of the electronic structure of wurtzite BeO

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Outline

- Motivations
- What is full-zone $k \cdot p$?
- Application to BeO
- Results and Discussion
- Conclusions



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Motivations

- $k \cdot p$ electronic structure model is important to study optical and transport properties of bulk semiconductor materials and low dimensional structures.
- Conventional $k \cdot p$ may be very accurate in the regions close to the band extrema, but it is not suitable to describe the electronic structure in the whole Brillouin Zone (BZ).
- It is desirable to have a method that maintains the simplicity of the conventional $k \cdot p$ but is accurate over the full BZ.
- We have developed a full-zone $k \cdot p$ model that attains this objectives and can be used for all those applications where a full-band description is needed.



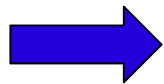
Why full-zone $k\cdot p$?

- Traditional approach beyond the basic effective mass approximation: “few-band” $k\cdot p$ (usually 6 or 8 bands for WZ, taking into account spin-orbit effects)
- Good representation close to a given point in the Brillouin Zone (usually Γ for direct-gap semiconductors)
- **Full-Brillouin-Zone** extension: satisfies requirements of accuracy in the entire BZ and for a wide range of energies



Full-zone $k \cdot p$

- $k \cdot p$ is an empirical method, which needs reliable experimental/ab initio reference data (*optimization targets*)



new calculations with ABINIT

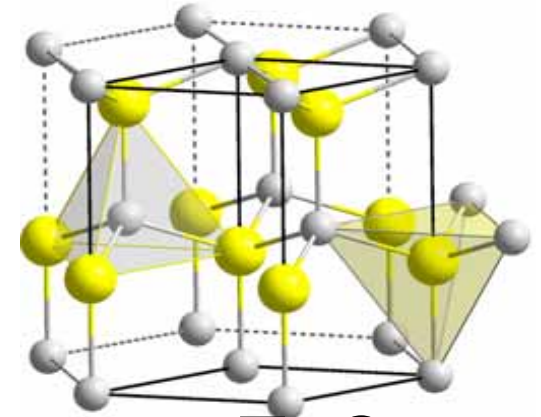
- The number of fitting parameters used by $k \cdot p$ must be minimized not to undermine its computational efficiency



development of a novel approach for FZ $k \cdot p$ in wurtzite crystals



BeO primer



- Very high energy gap (10.6 eV)
- Hexagonal lattice + lattice constant near ZnO
 - ➔ alloy with ZnO and BeZnO/ZnO QW
- Recent interest in BeZnO/ZnO light-emitting diodes and lasers
 - ➔ several theoretical and experimental works on BeO/BeZnO properties since 2006

[1] Y. R. Ryu, T. S. Lee, J. A. Lubguban, H. W. White, B.-J. Kim, Y.-S. Park, and C.-J. Youn, Appl. Phys. Lett., vol. 88, p. 241108(3), Jun. 2006.

[2] S. F. Ding, G. H. Fan, S. T. Li, K. Chen, and B. Xiao, Physica B, vol. 394, pp. 127–131, 2007.

[3] Y. Duan, H. Shi, and L. Qin, Phys. Lett. A, vol. 372, pp. 2930-2933, 2008.



Full-zone $k\cdot p$: application to Wurtzite Crystals

- We are interested in studying optical and transport properties of ternary alloy BeZnO
- The first step is the analysis of the electronic structure of the binary compounds: BeO and ZnO
- We need an accurate yet computationally efficient method suitable for inclusion e.g. in laser/LED design tools or in full-band Monte Carlo transport simulation

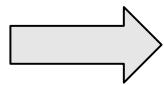


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development of a novel approach for
FZ $k \cdot p$ in wurtzite crystals



Reference data for $k \cdot p$: ABINIT

- We have performed DFT calculations on BeO with ABINIT using GGA pseudopotentials (cut-off energy: 40 Ha, 6x6x6 integration grid over the BZ)
- Energy gap = 7.7085 eV (target: 10.6 eV)
- Converged lattice constants and internal parameter:
 - $a = 2.6945 \text{ \AA}$ (exp. [1]: $a = 2.698 \text{ \AA}$ LDA [2]: $a = 2.664 \text{ \AA}$)
 - $c = 4.3751 \text{ \AA}$ (exp. [1]: $c = 4.380 \text{ \AA}$ LDA [2]: $c = 4.337 \text{ \AA}$)
 - $u = 0.3793$ (exp. [1]: $u = 0.378$ LDA [2]: $u = 0.377$)

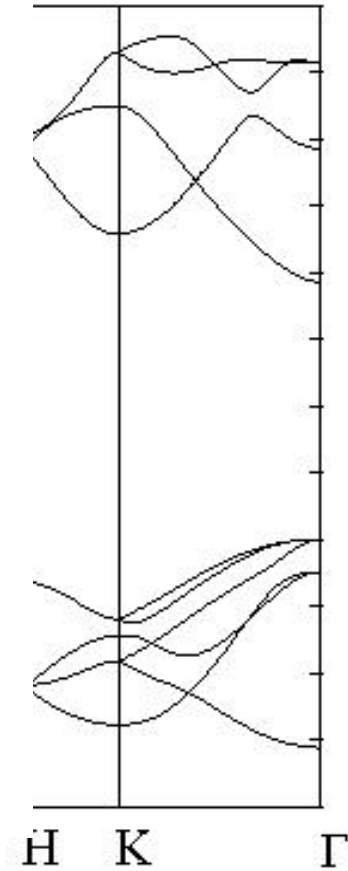
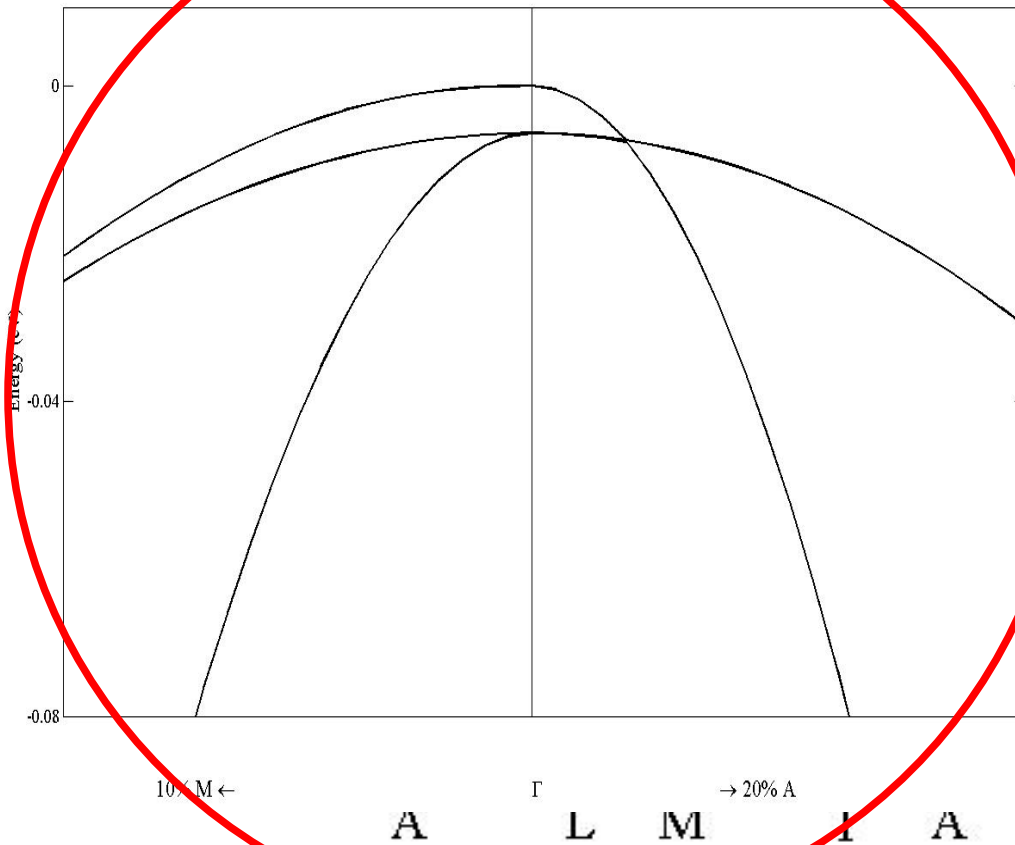
[1] Y.-N. Xu and W. Y. Ching, “Electronic, optical, and structural properties of some wurtzite crystals,” *Phys. Rev. B*, vol. 48, no. 7, pp. 4335–4351, Aug. 1993.

[2] B. Baumeier, P. Krüger, and J. Pollmann, “Atomic and electronic structure of BeO and the BeO (1010) surface: An *ab initio* investigation”, *Phys. Rev. B*, vol. 75, no. 04, pp. 5323–5330, 2007.



Reference data for $k \cdot p$: ABINIT

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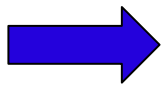
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2- developement of a novel approach for FZ $k \cdot p$ in wurtzite crystals



$k \cdot p$ basics

Based on Bloch theorem to solve Schrödinger equation

$$\psi(\mathbf{x}) = e^{i\mathbf{k} \cdot \mathbf{x}} u(\mathbf{x}) \quad + \quad \mathcal{H}\psi(\mathbf{x}) = E \psi(\mathbf{x})$$

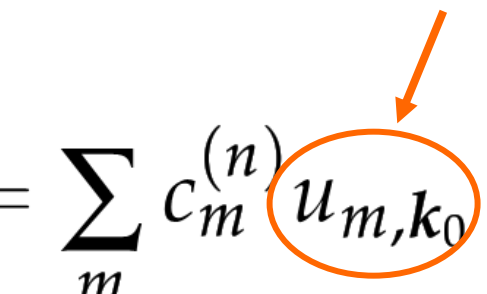
$$=$$

$$\left(\frac{\hbar^2 k^2}{2m_0} + \frac{\hbar}{m_0} \mathbf{k} \cdot \mathbf{p} + \frac{\hbar^2}{2m_0} \mathbf{p}^2 + V \right) u_{n,\mathbf{k}} = E_n u_{n,\mathbf{k}}$$

(with $\mathbf{p} = -i\hbar \nabla$)

basis functions

Method: series expansion of u

$$u_{n,\mathbf{k}} = \sum_m c_m^{(n)} u_{m,\mathbf{k}_0}$$




$k \cdot p$ basics

Final equation: eigenvalues problem

$$H(\mathbf{k})\mathbf{c}^{(n)} = E_n(\mathbf{k})\mathbf{c}^{(n)}$$

with

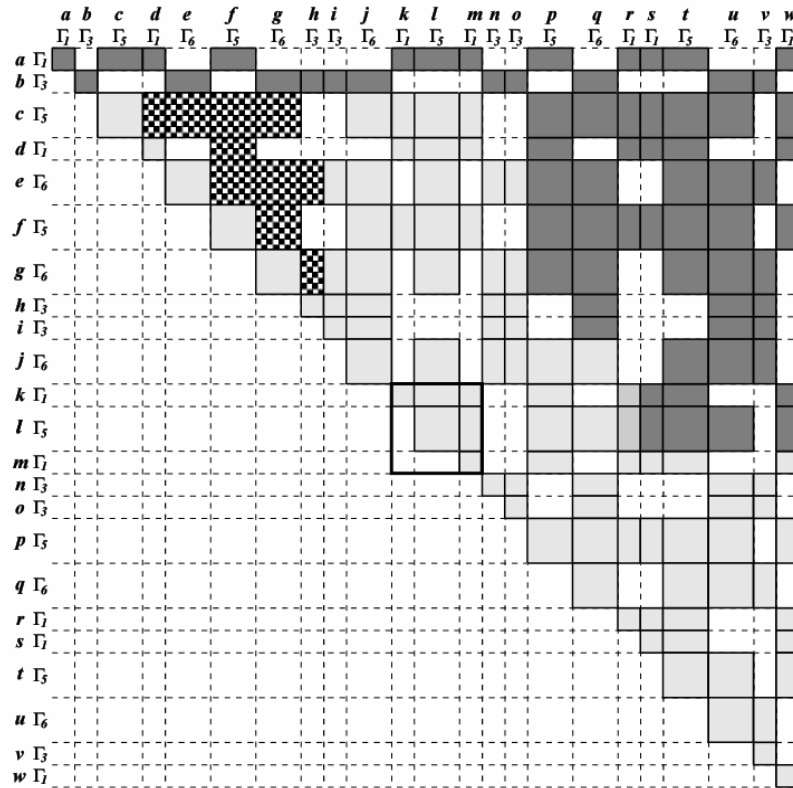
$$h_{m'm} = \left(E + \frac{\hbar^2}{2m_0} \|\mathbf{k} - \mathbf{k}_0\|^2 \right) \delta_{m'm} + \frac{\hbar}{m_0} \langle \psi_{m',\mathbf{k}} | (\mathbf{k} - \mathbf{k}_0) \cdot \mathbf{p} | \psi_{m',\mathbf{k}} \rangle$$

Determining h coefficients:

- directly from definition (knowing wavefunctions)
- fit (exploiting crystal **symmetries**)



First FZ $k \cdot p$ improvement: Wurtzite symmetries in Γ

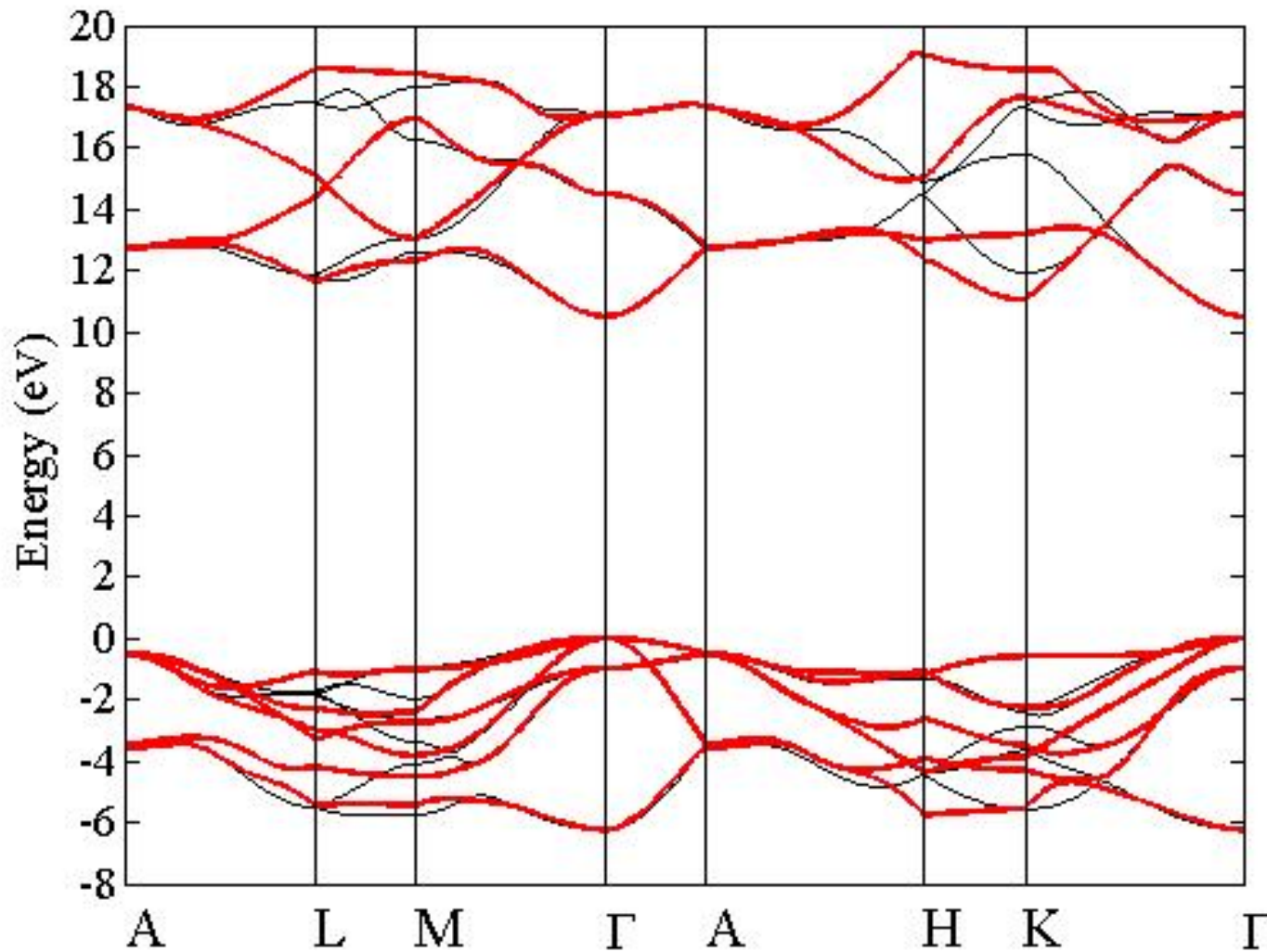


	$E(g_0)$	$C_2(\tilde{g}_3)$	$2C_3(g_2)$	$2C_6(\tilde{g}_1)$	$3\sigma_d(g_6)$	$3\sigma'_d(\tilde{g}_9)$
Γ_1	(1)	(1)	(1)	(1)	(1)	(1)
Γ_3	(1)	(-1)	(1)	(-1)	(1)	(-1)
Γ_5	$\begin{pmatrix} 1 & 0 \\ 0 & 1 \end{pmatrix}$	$\begin{pmatrix} -1 & 0 \\ 0 & -1 \end{pmatrix}$	$\begin{pmatrix} -1/2 & -\sqrt{3}/2 \\ \sqrt{3}/2 & -1/2 \end{pmatrix}$	$\begin{pmatrix} 1/2 & -\sqrt{3}/2 \\ \sqrt{3}/2 & 1/2 \end{pmatrix}$	$\begin{pmatrix} 1 & 0 \\ 0 & -1 \end{pmatrix}$	$\begin{pmatrix} -1 & 0 \\ 0 & 1 \end{pmatrix}$
Γ_6	$\begin{pmatrix} 1 & 0 \\ 0 & 1 \end{pmatrix}$	$\begin{pmatrix} 1 & 0 \\ 0 & 1 \end{pmatrix}$	$\begin{pmatrix} -1/2 & -\sqrt{3}/2 \\ -\sqrt{3}/2 & -1/2 \end{pmatrix}$	$\begin{pmatrix} -1/2 & -\sqrt{3}/2 \\ \sqrt{3}/2 & -1/2 \end{pmatrix}$	$\begin{pmatrix} 1 & 0 \\ 0 & -1 \end{pmatrix}$	$\begin{pmatrix} 1 & 0 \\ 0 & -1 \end{pmatrix}$

- Periodic functions on Bravais solid ($k = 0$)
- Decomposition in **representations**



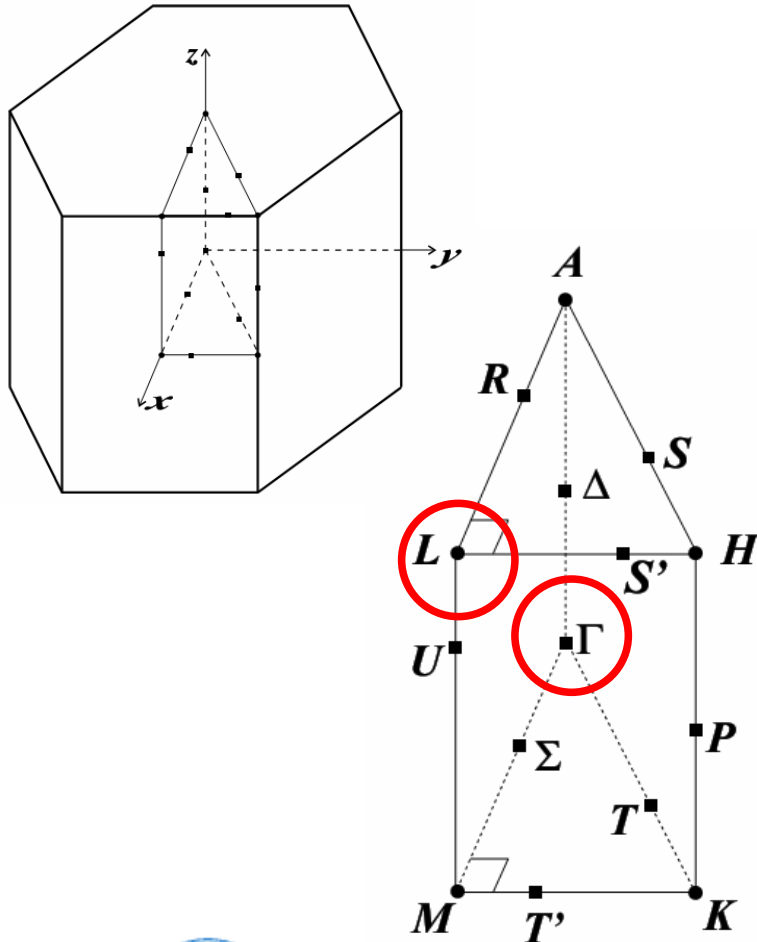
Limitations of single-point $k \cdot p$ full-zone



Energy inaccuracies far from Γ when using the standard $k \cdot p$ single point expansion



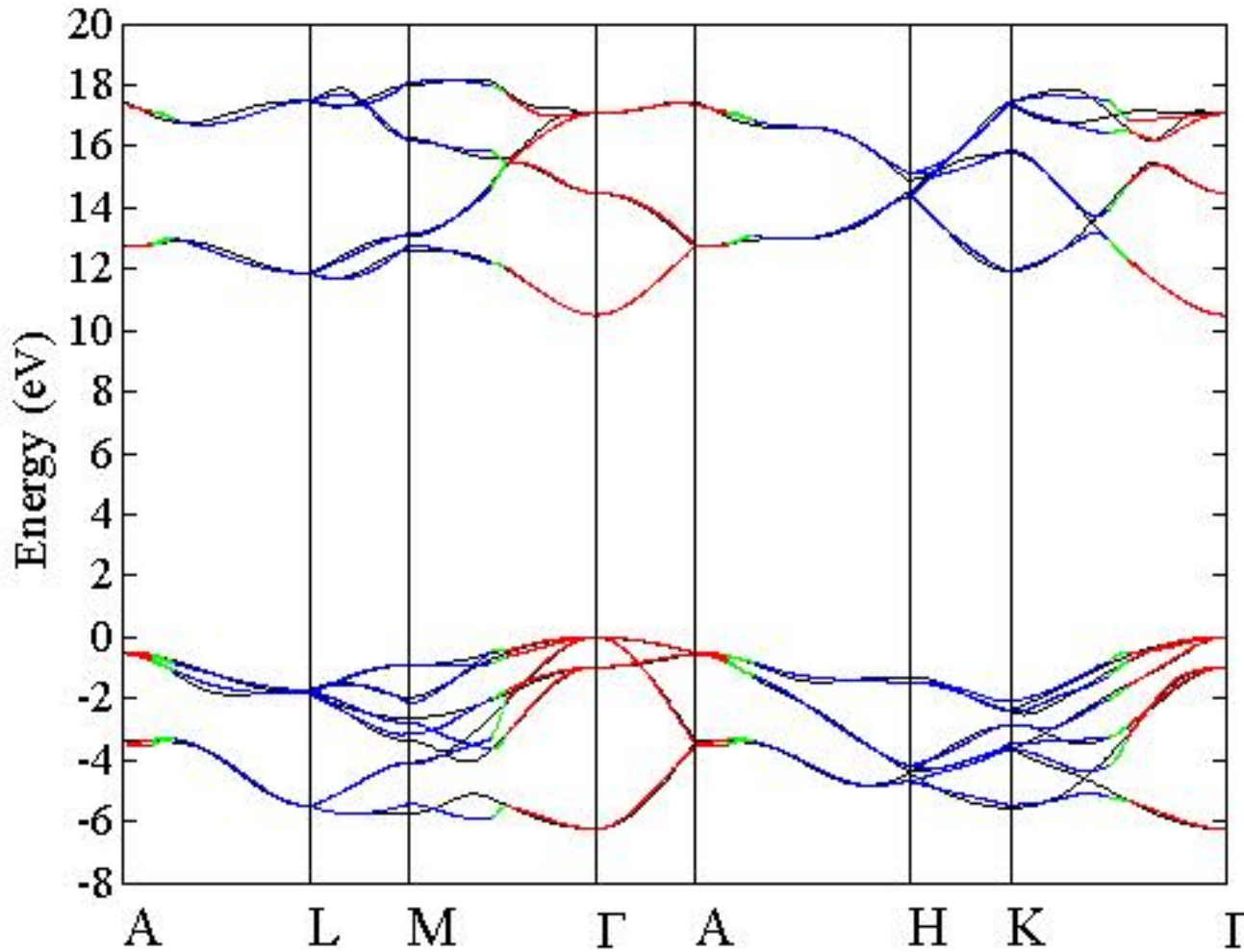
Second FZ $k \cdot p$ improvement: Two expansion points



- We have performed two $k \cdot p$ calculations using two expansion points: the first in Γ and the second in L
- 6 valence bands and 4 conduction bands



$k \cdot p$ vs. ABINIT



ABINIT
(with the so-called
scissor correction)

$k \cdot p$ in Γ

$k \cdot p$ in L

*Two-expansion
point $k \cdot p$*



Conclusions

- We have developed a novel full-zone $k \cdot p$ approach for wurtzite crystals based on multi-k-point expansion.
- This approach makes it possible to significantly improve the precision of the conventional $k \cdot p$ method over the full BZ.
- We presently applying this technique to several wurtzite materials (III-Nitrides and II-VI Oxides).
- As presented for BeO the novel approach leads to full zone $k \cdot p$ electronic structure with overall quality comparable with *ab initio* methods.

